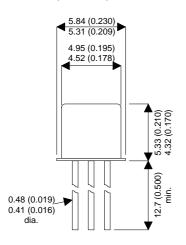
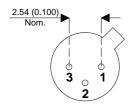




MECHANICAL DATA

Dimensions in mm (inches)





TO-18 METAL PACKAGE Underside View

PIN 3 - Collector PIN 1 - Emitter PIN 2 - Base

PNP SILICON TRANSISTOR

FEATURES

- PNP High Voltage Planar Transistor
- Hermetic TO18 Package
- Full Screening Options Available

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

$\overline{V_{CBO}}$	Collector – Base Voltage	-150V
V_{CEO}	Collector – Emitter Voltage (I _B = 0)	-150V
V_{EBO}	Emitter – Base Voltage (I _B = 0)	-6V
$I_{\mathbb{C}}$	Collector Current	0.1A
P_{D}	Total Device Dissipation T _A = 25 °C	0.4W
P_{D}	Total Device Dissipation T _C = 25 °C	1.4W
T_{stg}	Storage Temperature	−55 to 200°C
T_{J}	Max Operating Junction Temperature	200°C
$R_{ hetaJA}$	Thermal Resistance Junction to Ambient	438°C/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	125°C/W

Semelab PIc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

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ELECTRICAL CHARACTERISTICS Continued ($T_A = 25$ °C unless otherwise stated)

	Parameter	Test Conditions	Min.	Тур.	Max.	Unit.
V _{(BR)CBO}	Collector - Base Breakdown Voltage (1)	$I_C = -10\mu A$, $I_E = 0$	-150			V
V _{(BR)CEO}	Collector - Emitter Breakdown Voltage (1)	I _C =- 2mA , I _B = 0	-150			V
I _{CBO}	Colllector Cut Off Current	Vcb = -100v, IE = 0		-0.2	-10	nA
		Vcb = -100v, IE = 0 TA =125 °C	-	-0.03	-10	μА
V _{(BR)EBO}	Emitter - Base Breakdown Voltage (1)	$I_E = -10\mu A$, $I_C = 0$	-6			V
V _{CE(sat)}	Collector - Emitter Saturation Voltage (1)	I _C =-10mA , I _B = -1mA		-0.1	-0.5	V
V _{BE(sat)}	Base - Emitter Saturation Voltage (1)	I _C =-10mA , I _B = -1mA		-0.74	-0.9	V
h _{FE}	DC Current Gain (1)	Ic =-1mA, VcE = -10v	40	85		
		Ic =-10mA, VcE = -10v Ic =-10μA, VcE = -10v	40	100 30		
f _T	Current Gain - Bandwith Product	I_{C} =-1mA , V_{CE} =-10v, f=20 MHz		50		MHz
		I _C =-10mA	60			
C _{EBO}	Emitter- Base Capacitance	$V_{EB} = -0.5 \text{ V}$, $I_{E} = 0$, $f = 1 \text{ MHz}$		20	25	pF
С _{СВО}	Collector- Base Capacitance	V_{CB} =-5v , I_E = 0 , f=1 MHz		5	7	pF

(1) Pulse test: Pulse Width < 300µs ,Duty Cycle < 2%

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